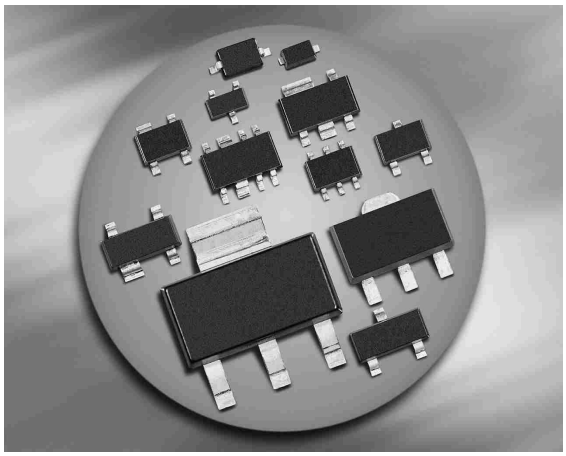
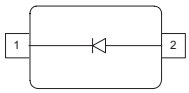
Silicon PIN Diode

- Optimized for antenna switches in hand held applications
- Very low capacitance at zero volts reverse bias at frequencies above 1GHz (typ. 0.19 pF)
- Low forward resistance (typ. 0.8Ω @ I_F = 10mA)
- Very low signal distortion



BAR89-02L



Type	Package	Configuration	L_S(nH)	Marking
BAR89-02L	TSLP-2-1	single, leadless	0.4	RS

Maximum Ratings at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	80	V
Forward current	I_F	100	mA
Total power dissipation $T_s \leq$ 133°C	P_{tot}	250	mW
Junction temperature	T_j	150	°C
Operating temperature range	T_{op}	-55 ... 125	
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)], BAR89-02L	R_{thJS}	≤ 65	K/W

[1]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Breakdown voltage $I_{(BR)}$ = 5 µA	$V_{(BR)}$	80	-	-	V
Reverse current V_R = 60 V	I_R	-	-	50	nA
Forward voltage	V_F				V
I_F = 10 mA		-	0.83	0.9	
I_F = 100 mA		-	0.95	1.1	

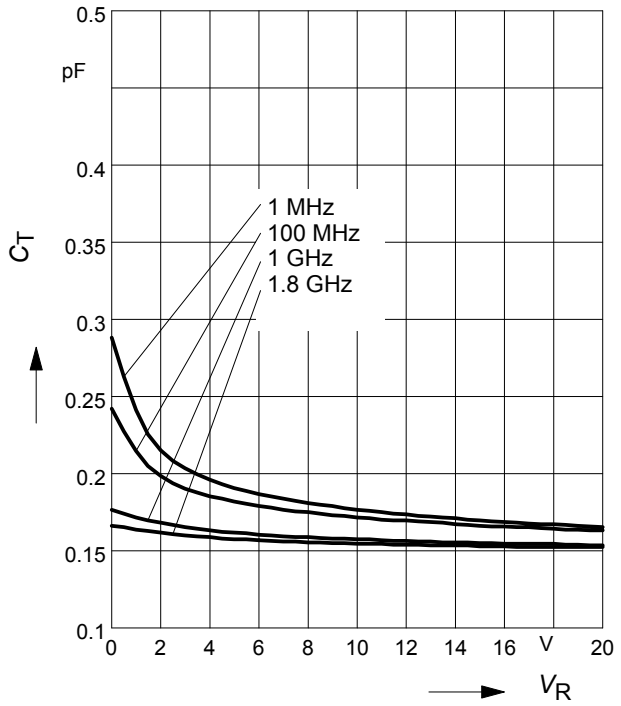
Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Diode capacitance	C_T				pF
V_R = 1 V, f = 1 MHz		-	0.25	0.35	
V_R = 0 V, f = 100 MHz		-	0.25	-	
V_R = 0 V, f = 1 GHz		-	0.19	-	
V_R = 0 V, f = 1.8 GHz		-	0.18	-	
Reverse parallel resistance	R_P				kΩ
V_R = 0 V, f = 100 MHz		-	35	-	
V_R = 0 V, f = 1 GHz		-	5	-	
V_R = 0 V, f = 1.8 GHz		-	3.5	-	
Forward resistance	r_f				Ω
I_F = 1 mA, f = 100 MHz		-	3	-	
I_F = 5 mA, f = 100 MHz		-	1.2	-	
I_F = 10 mA, f = 100 MHz		-	0.8	1.5	
Charge carrier life time	τ_{rr}	-	800	-	ns
I_F = 10 mA, I_R = 6 mA, measured at I_R = 3 mA, R_L = 100 Ω					
I-region width	W_I	-	19	-	µm
Insertion loss[1)]	$\|S_{21}\|^2$				dB
I_F = 1 mA, f = 1.8 GHz		-	-0.23	-	
I_F = 5 mA, f = 1.8 GHz		-	-0.1	-	
I_F = 10 mA, f = 1.8 GHz		-	-0.08	-	
Isolation[1)]	$\|S_{21}\|^2$				
V_R = 0 V, f = 0.9 GHz		-	-19	-	
V_R = 0 V, f = 1.8 GHz		-	-14	-	
V_R = 0 V, f = 2.45 GHz		-	-11	-	

[1]BAR89-02L in series configuration, Z = 50Ω

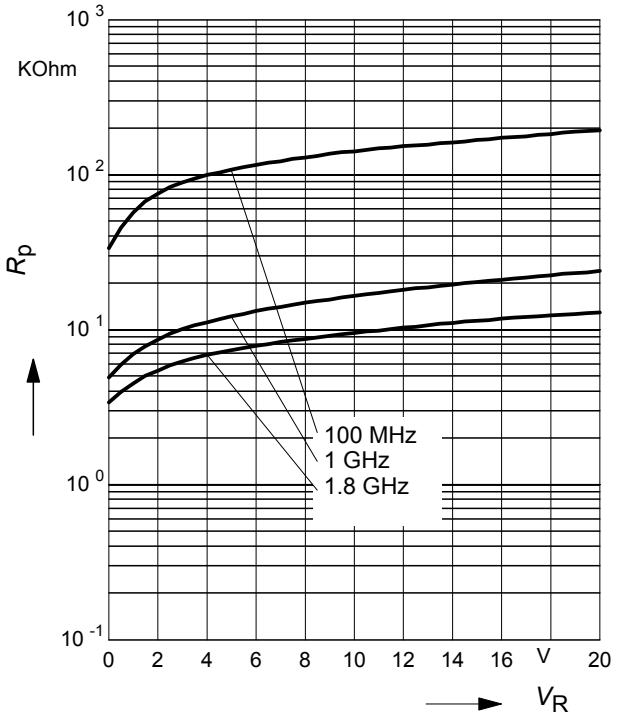
Diode capacitance $C_T = f\ (V_R)$

f = Parameter



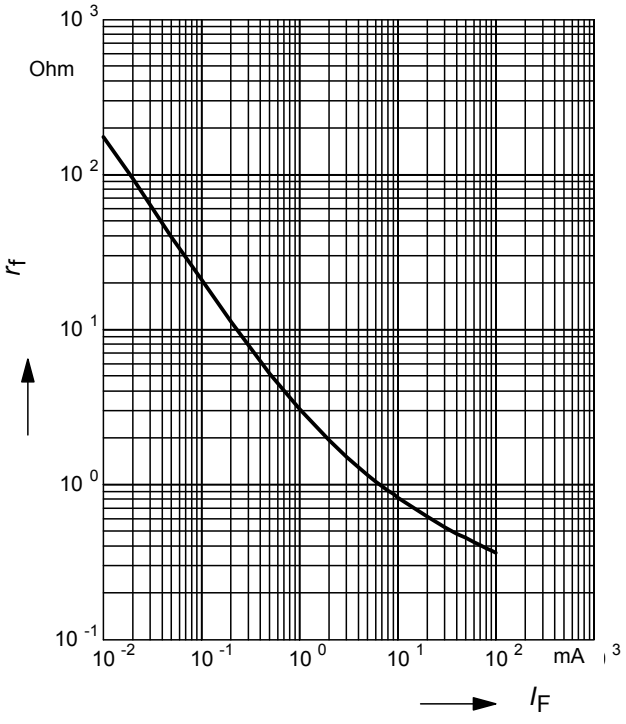
Reverse parallel resistance $R_P = f(V_R)$

f = Parameter



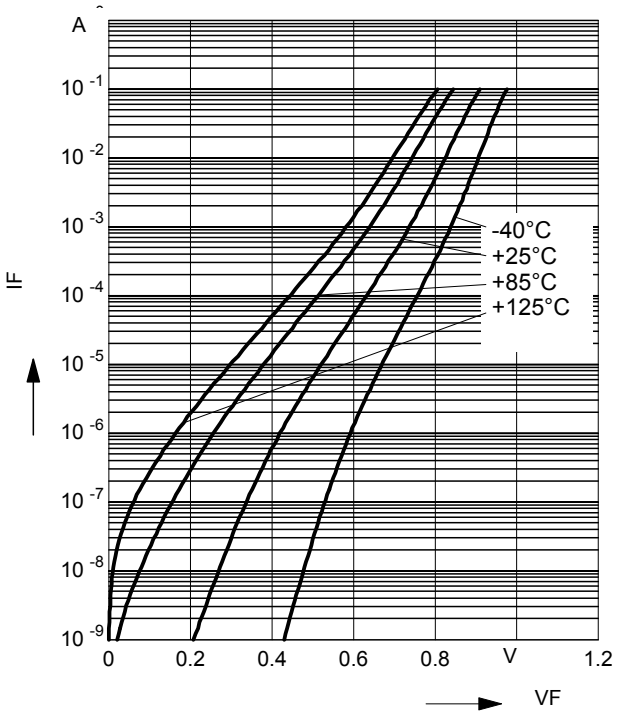
Forward resistance $r_f = f\ (I_F)$

f = 100MHz



Forward current $I_F = f\ (V_F)$

T_A = Parameter



Forward current $I_F = f(T_S)$

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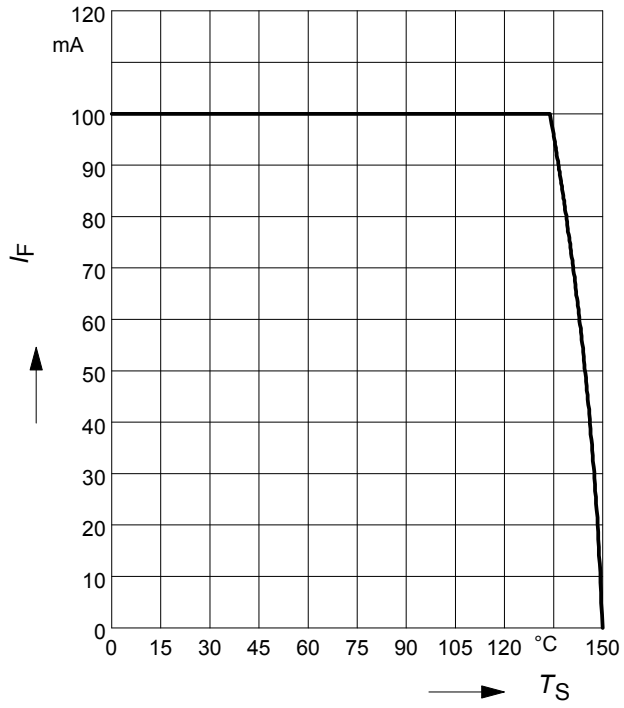
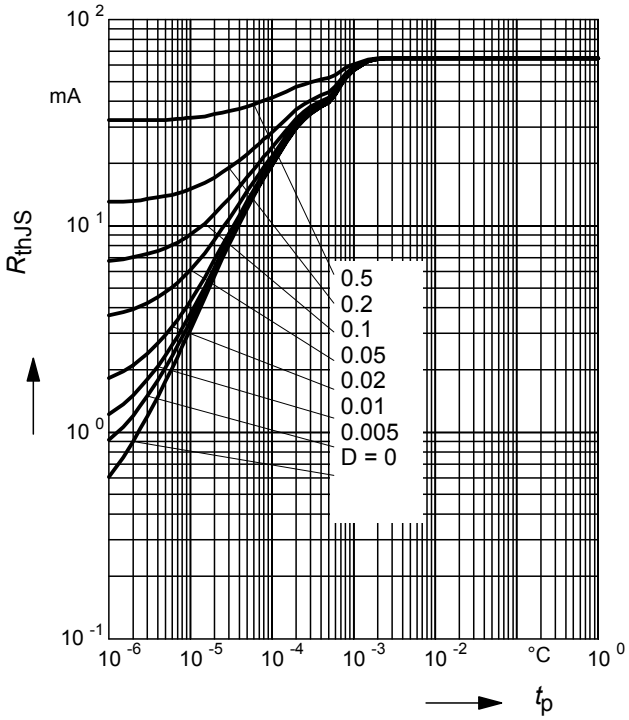


Permissible Puls Load $R_{thJS} = f(t_p)$

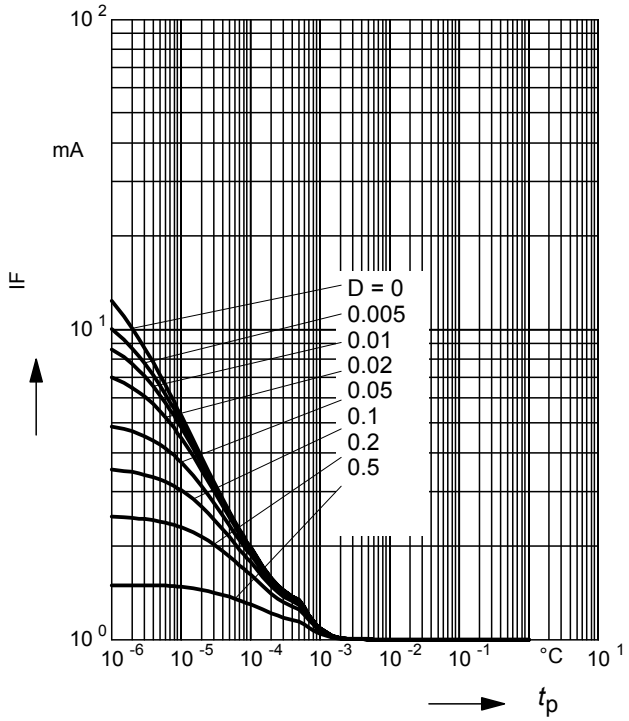
BAR89-02L



Permissible Pulse Load

$I_{Fmax}/ I_{FDC} = f(t_p)$

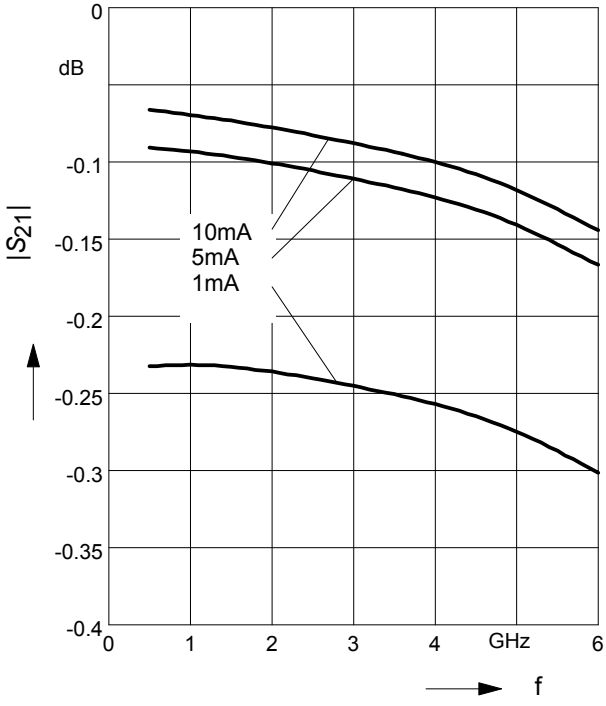
BAR89-02L



Insertion loss $|S_{21}|^2 = f(f)$

I_F = Parameter

BAR89-02L in series configuration, $Z = 50\Omega$



Isolation $|S_{21}|^2 = f(f)$

V_R = Parameter

BAR89-02L in series configuration, $Z = 50\Omega$